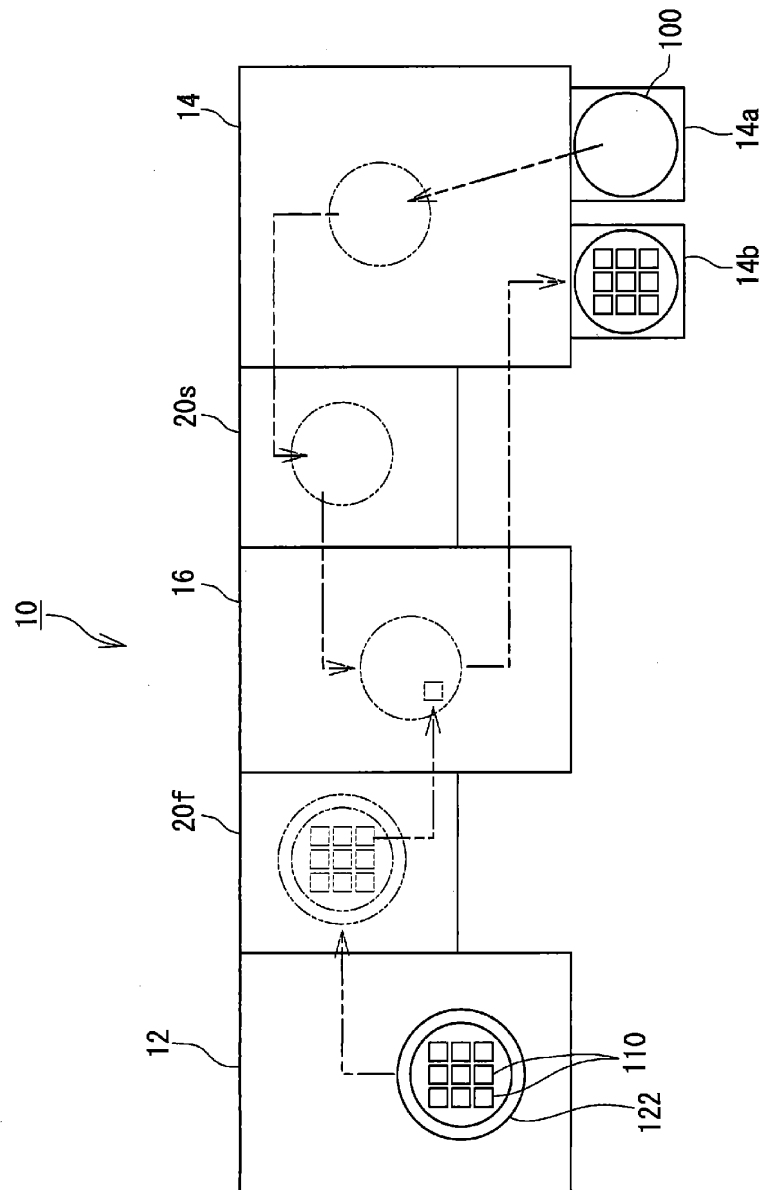
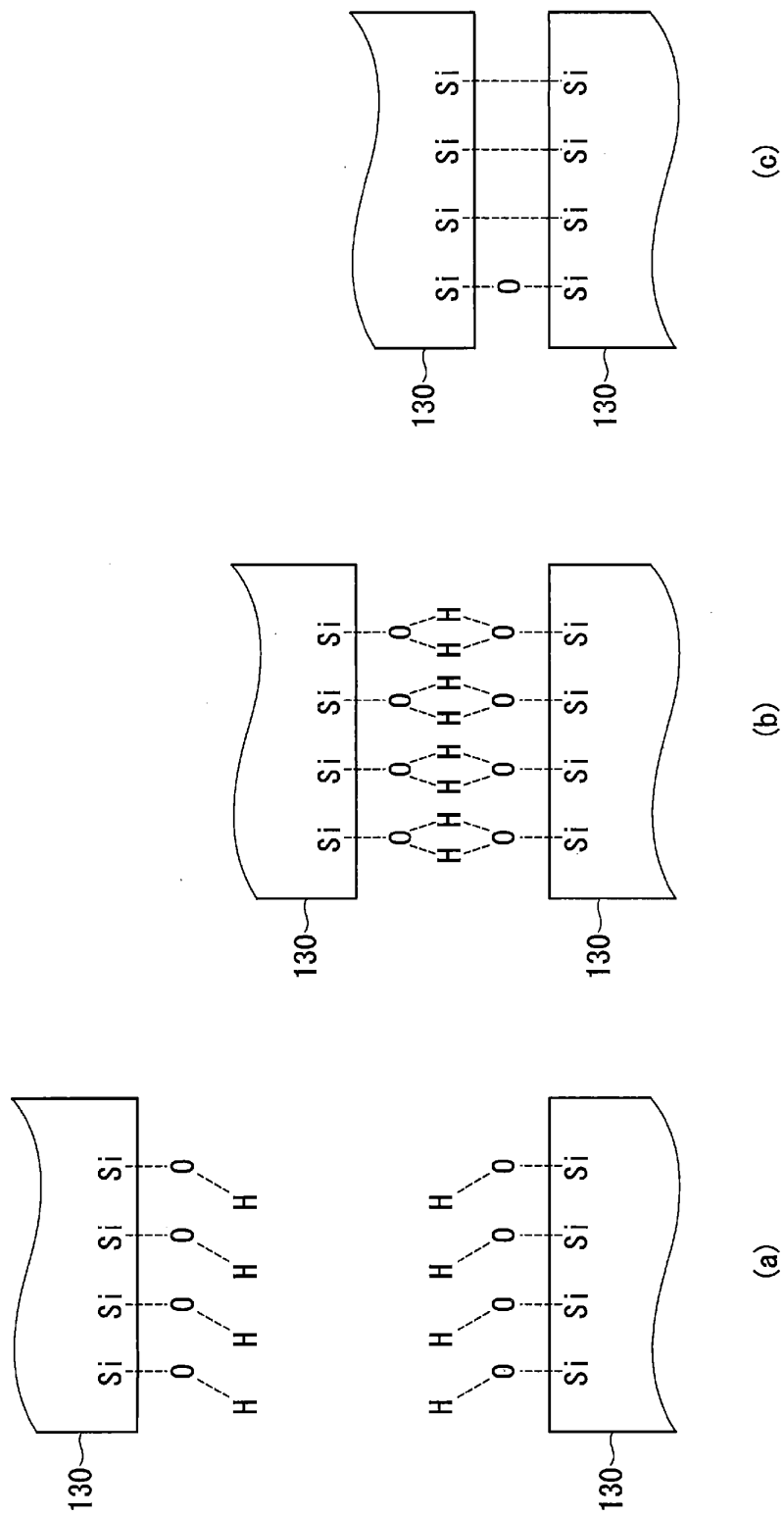


[図1]

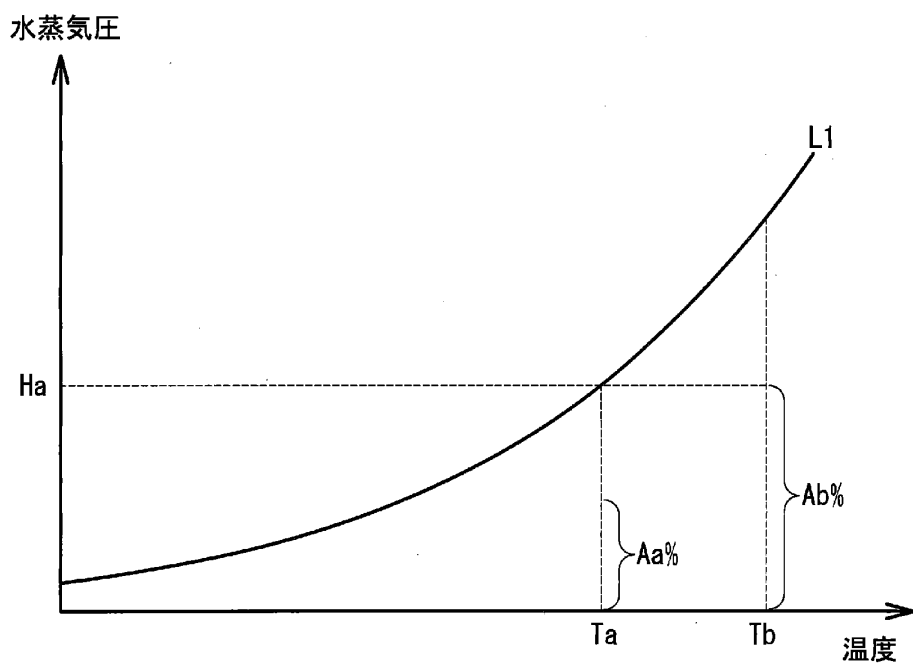


A cross-sectional view of a semiconductor device. A substrate 100 is shown at the bottom. Three patterns 110 are formed on the substrate. The left pattern 110 has four openings 112, the middle pattern 110 has two openings 112, and the right pattern 110 has two openings 112. The openings 112 are filled with a material 102.

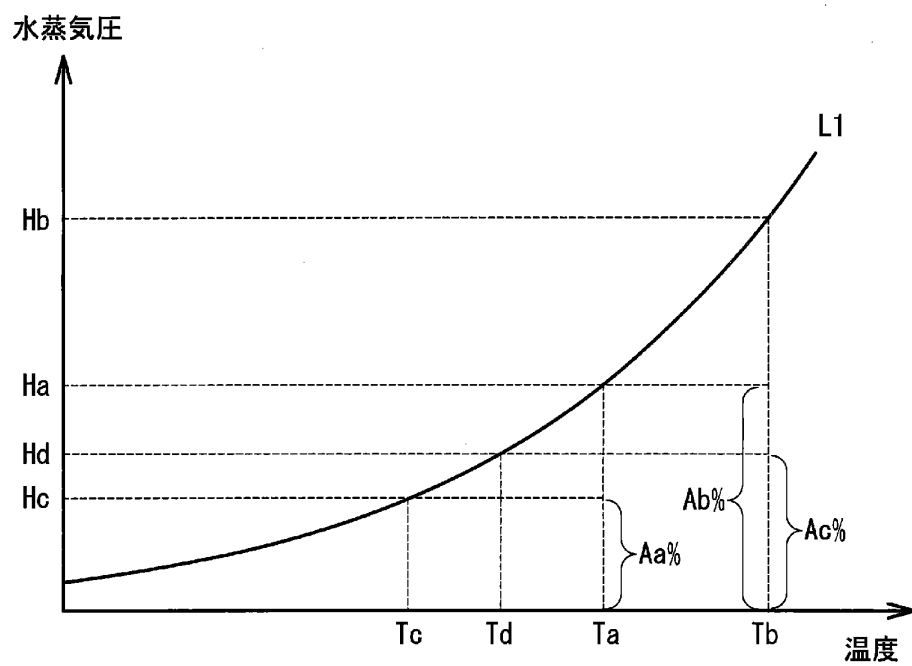
[図4]



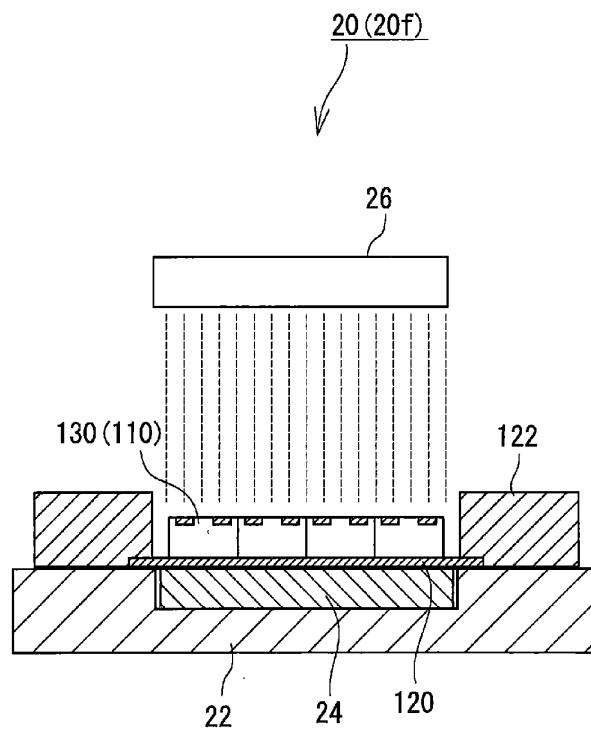
[図5]



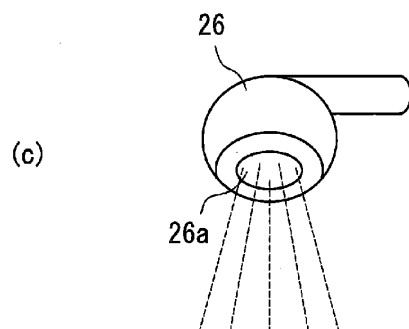
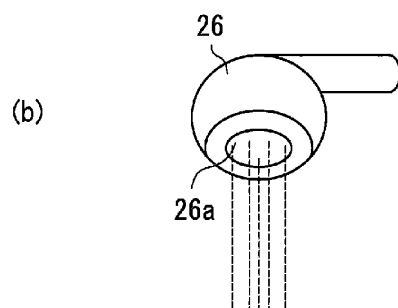
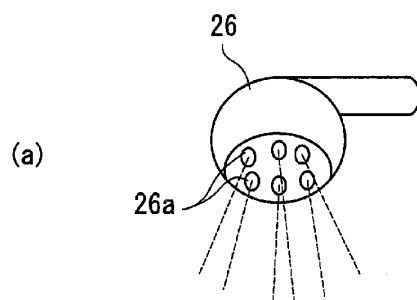
[図6]



[図7]



[図8]



[図9]

